

GENERAL DESCRIPTION

This planer stripe MOSFET has better characteristics, such as fast switching time, low on resistance, low gate charge and excellent avalanche characteristics. It is mainly suitable for portable equipment and SMPS.

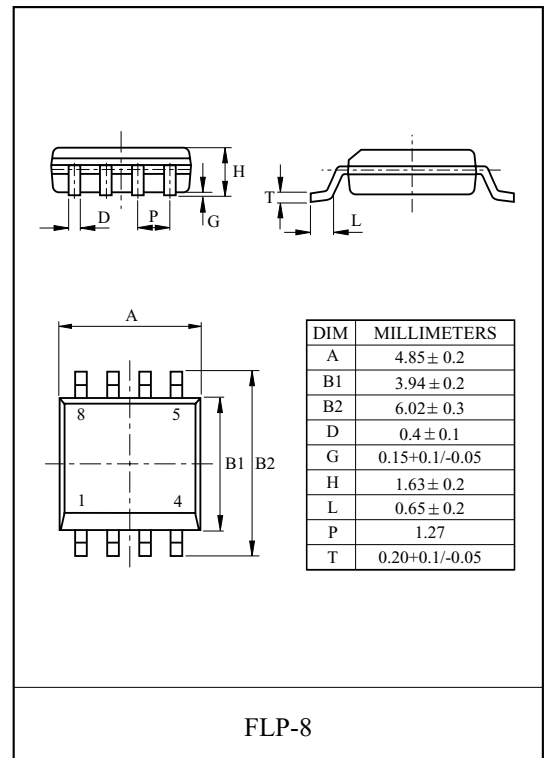
FEATURES

- $V_{DSS}=30V, I_D=6A.$
- Drain-Source ON Resistance.
 $R_{DS(ON)}=28m\ \Omega$ (Max.) @ $V_{GS}=10V$
 $R_{DS(ON)}=42m\ \Omega$ (Max.) @ $V_{GS}=4.5V$
- Super High Dense Cell Design
- High Power and Current Handling Capability

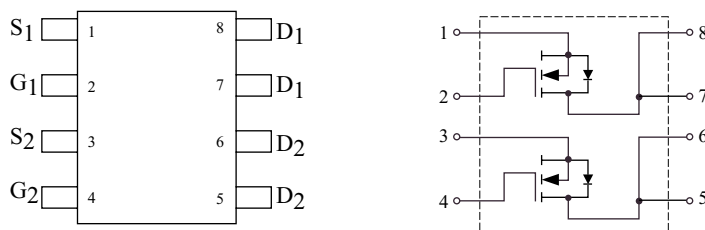
MAXIMUM RATING (Ta=25 °C Unless otherwise noted)

CHARACTERISTIC		SYMBOL	PATING	UNIT
Drain Source Voltage		V_{DSS}	30	V
Gate Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D^*	6	A
	Pulsed (note1)	I_{DP}	20	A
Drain Source Diode Forward Current		I_S	1.3	A
Drain Power Dissipation	25 °C	P_D^*	2	W
	100 °C		1.6	W
Maximum Junction Temperature		T_j	-50~150	°C
Storage Temperature Range		T_{stg}	-50~150	°C
Thermal Resistance, Junction to Ambient		R_{thJA}^*	78	°C/W

* : Surface Mounted on FR4 Board, $t \leq 10sec.$



PIN CONNECTION (TOP VIEW)



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ELECTRICAL CHARACTERISTICS (Ta=25°C) UNLESS OTHERWISE NOTED

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	30	-	-	V
Drain Cut-off Current	I_{DSS}	$V_{DS}=24V, V_{GS}=0V$	-	-	1	μA
Gate Leakage Current	I_{GSS}	$V_{GS}=\pm 25V, V_{DS}=0V$	-	-	± 100	μA
Gate Threshold Voltage	V_{th}	$V_{DS}=V_{GS}, I_D=250\mu A$	1	2	3	V
Drain-Source ON Resistance	$R_{DS(ON)}$	$V_{GS}=10.0V, I_D=6A$	-	24	28	m Ω
		$V_{GS}=4.5V, I_D=4.9A$	-	35	42	
On-State Drain Current	$I_{D(ON)}$	$V_{DS}=5V, V_{GS}=10A$	20	-	-	A
Forward Transconductance	G_{fs}	$V_{DS}=10V, I_D=6A$	-	20	-	S
Dynamic (Note 3)						
Input Capacitance	C_{iss}	$V_{DS}=15V, f=1MHz, V_{GS}=0V$	-	740	-	pF
Output Capacitance	C_{oss}		-	170	-	
Reverse Transfer Capacitance	C_{rss}		-	75	-	
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=5V, I_D=6A$	-	7	10	nC
Gate-Source Charge	Q_{gs}		-	3.8	-	
Gate-Drain Charge	Q_{gd}		-	2.5	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=15V, V_{GS}=10V$ $I_D=1A, R_G=6\Omega$ (Note 1)	-	8	16	ns
Turn-On Rise Time	t_r		-	13	24	
Turn-On Delay Time	$t_{d(off)}$		-	18	29	
Turn-On Fall Time	t_f		-	8	6	
Source-Drain Diode Ratings						
Source-Drain Forward Voltage	V_{SDF}	$I_{DR}=1.7A, V_{GS}=0V$	-	0.75	1.2	V
Note						
1. Pulse Test : Pulse width $\leq 10\mu s$, Duty cycle $\leq 1\%$						

* Upper electrical characteristics can be changed because these are tentative specifications.

* Graphs are omitted because these are tentative specifications.

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Fig1. $I_D - V_{DS}$

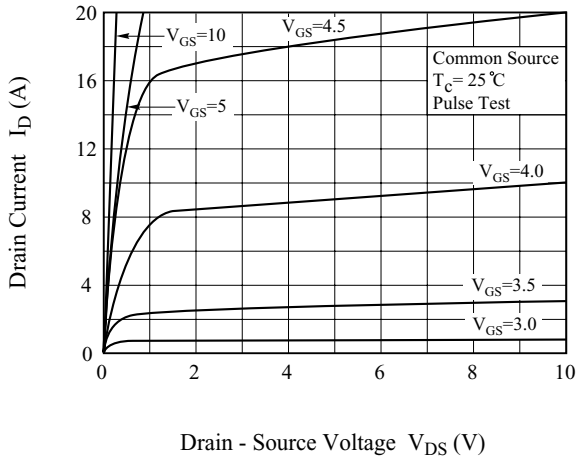


Fig2. $R_{DS(on)} - I_D$

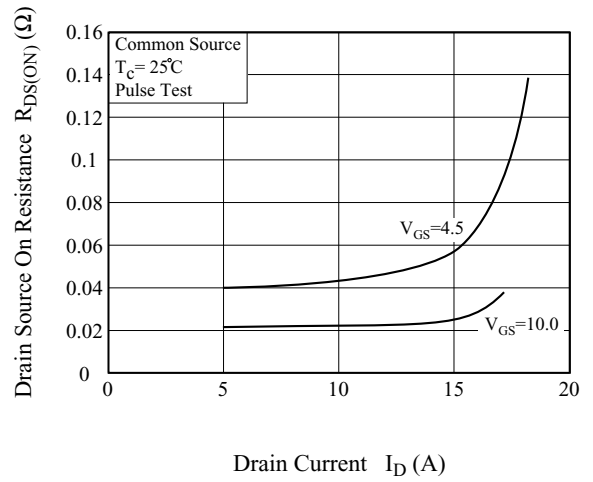


Fig3. $I_D - V_{GS}$

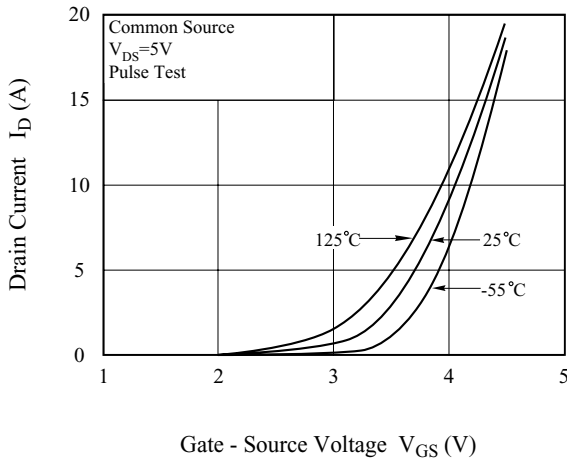


Fig4. $R_{DS(on)} - T_j$

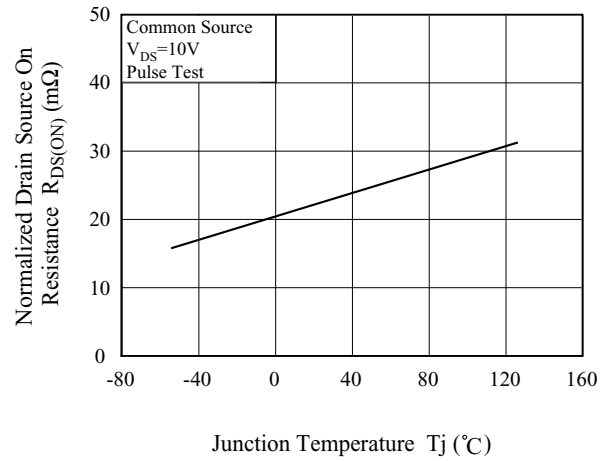


Fig5. $V_{th} - T_j$

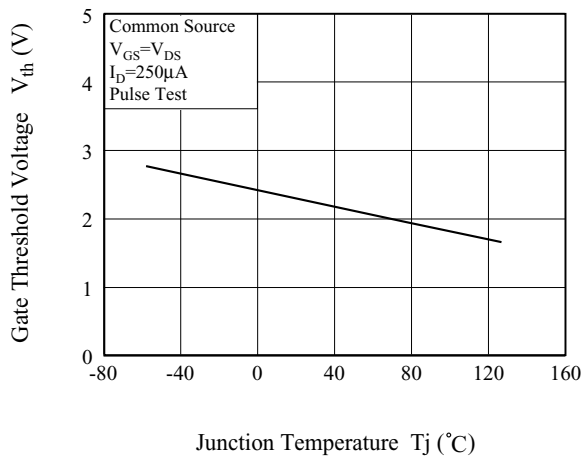
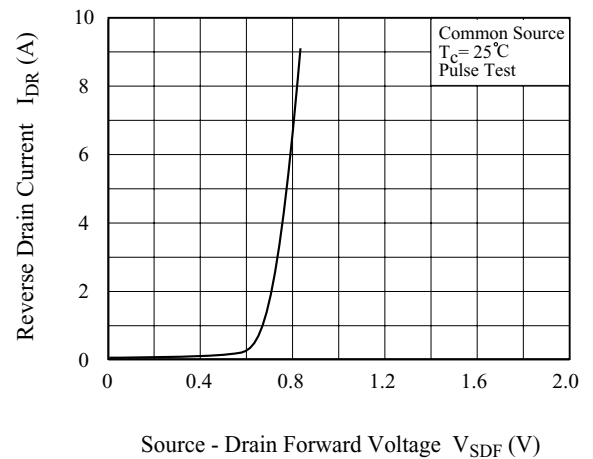


Fig6. $I_{DR} - V_{SDF}$



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Fig7. Transient Thermal Response Curve

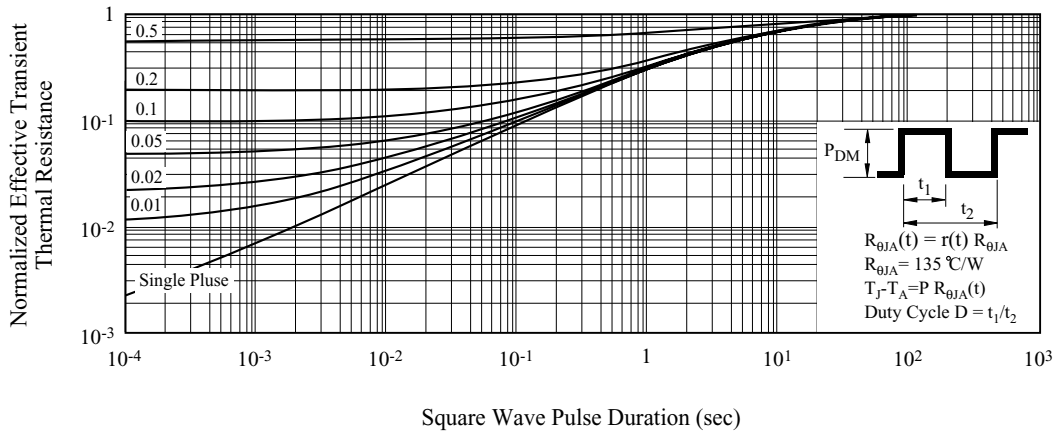
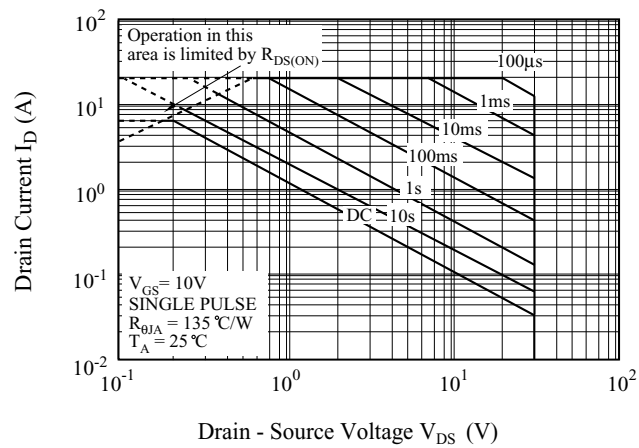


Fig8. Safe Operation Area



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Fig. 9 Gate Charge

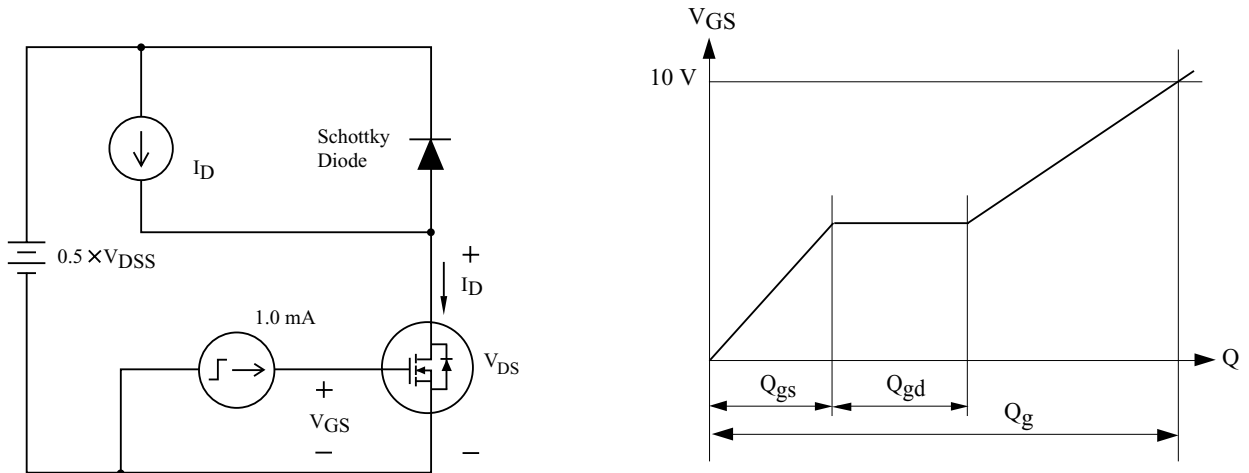


Fig. 10 Resistive Load Switching

